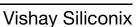
COMPLIANT HALOGEN

**FREE** 





## N-Channel 40 V (D-S) 150 °C MOSFET



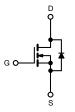
PRODUCT SUMMARY				
V <sub>DS</sub> (V)	40			
$R_{DS(on)}$ max. ( $\Omega$ ) at $V_{GS} = 10 \text{ V}$	0.00399			
$R_{DS(on)}$ max. ( $\Omega$ ) at $V_{GS} = 4.5 \text{ V}$	0.0060			
Q <sub>g</sub> typ. (nC)	12.4			
I <sub>D</sub> (A) <sup>a</sup>	81.2			
Configuration	Single			

#### **FEATURES**

- TrenchFET® Gen IV power MOSFET
- Tuned for the lowest R<sub>DS</sub>-Q<sub>oss</sub> FOM
- 100 % R<sub>q</sub> and UIS tested
- Q<sub>qd</sub>/Q<sub>qs</sub> ratio < 1 optimizes switching characteristics</li>
- · Optimized for wave soldering
- · Flexible leads increase resilience to board flexing
- Material categorization: for definitions of compliance please see <a href="https://www.vishay.com/doc?99912"><u>www.vishay.com/doc?99912</u></a>

#### **APPLICATIONS**

- Synchronous rectification
- High power density DC/DC
- DC/AC inverters
- · Switch mode power supplies



N-Channel MOSFET

ORDERING INFORMATION	
Package	PowerPAK SO-8L
Lead (Pb)-free and halogen-free	SiJA74DP-T1-GE3

ABSOLUTE MAXIMUM RATING	<b>iS</b> (T <sub>A</sub> = 25 °C, u	nless other	wise noted)		
PARAMETER		SYMBOL	LIMIT	UNIT	
Drain-source voltage		V <sub>DS</sub>	40	V	
Gate-source voltage		$V_{GS}$	+20 / -16	v	
	T <sub>C</sub> = 25 °C		81.2		
Continuous drain surrent (T = 150 °C)	T <sub>C</sub> = 70 °C	1	64.2		
Continuous drain current (T <sub>J</sub> = 150 °C)	T <sub>A</sub> = 25 °C	l <sub>D</sub>	24 <sup>b</sup>		
	T <sub>A</sub> = 70 °C		19.2 <sup>b</sup>	^	
Pulsed drain current (t = 100 μs)		I <sub>DM</sub>	150	A	
Continuous survey during displacement	T <sub>C</sub> = 25 °C		42		
Continuous source-drain diode current	T <sub>A</sub> = 25 °C	l <sub>S</sub>	3.7 b, c		
Single pulse avalanche current	diode current $T_C = 25 ^{\circ}\text{C}$ $T_A = 25 ^{\circ}\text{C}$ Furrent $T_C = 25 ^{\circ}\text{C}$ $T_A = 25 ^{\circ}\text{C}$		20		
Single pulse avalanche energy	L=0.1 mn	E <sub>AS</sub>	20	mJ	
	T <sub>C</sub> = 25 °C		46.2		
Marriagona a consulada de esta esta esta esta esta esta esta est	T <sub>C</sub> = 70 °C 29	29.6	14/		
Maximum power dissipation	T <sub>A</sub> = 25 °C	P <sub>D</sub>	4.1 <sup>b</sup>	W	- vv
	T <sub>A</sub> =70 °C		2.6 b		
Operating junction and storage temperature range		T <sub>J</sub> , T <sub>stg</sub>	-55 to +150	°C	
Soldering recommendations (peak temperature) c		J	260	-0	

THERMAL RESISTANCE RAT	NGS				
PARAMETER		SYMBOL	TYPICAL	MAXIMUM	UNIT
Maximum junction-to-ambient <sup>b</sup>	t < 10 s	R <sub>thJA</sub>	25	30	°C/W
Maximum junction-to-case (drain)	Steady state	$R_{thJC}$	2.1	2.7	C/VV

#### Notes

- a.  $T_C = 25$  °C
- b. Surface mounted on 1" x 1" FR4 board
- c. t = 10 s
- d. See solder profile (www.vishay.com/doc?73257). The PowerPAK SO-8L is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection
- e. Rework conditions: manual soldering with a soldering iron is not recommended for leadless components
- f. Maximum under steady state conditions is 75 °C/W



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# Vishay Siliconix

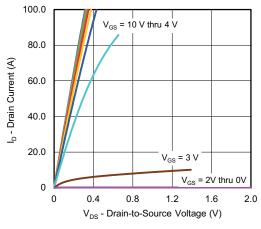
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
Static						
Drain-source breakdown voltage	V <sub>DS</sub>	$V_{GS} = 0 \text{ V}, I_D = 250 \mu\text{A}$	40	-	-	V
V <sub>DS</sub> temperature coefficient	$\Delta V_{DS}/T_{J}$	I <sub>D</sub> = 1 mA	-	24	-	
V <sub>GS(th)</sub> temperature coefficient	$\Delta V_{GS(th)}/T_J$	I <sub>D</sub> = 250 μA	-	-6.1	-	mv/°C
Gate-source threshold voltage	V <sub>GS(th)</sub>	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	1.0	-	2.4	V
Gate-source leakage	I <sub>GSS</sub>	$V_{DS} = 0 \text{ V}, V_{GS} = +20 \text{ / -16 V}$	-	-	100	nA
Zoro goto voltogo droin overent		V <sub>DS</sub> = 40 V, V <sub>GS</sub> =0 V	-	-	1	
Zero gate voltage drain current	I <sub>DSS</sub>	V <sub>DS</sub> = 40 V, V <sub>GS</sub> = 0 V, T <sub>J</sub> = 70 °C	-	-	15	μΑ
On-state drain current <sup>a</sup>	I <sub>D(on)</sub>	$V_{DS} \ge 10 \text{ V}, V_{GS} = 10 \text{ V}$	30	-	-	Α
Drain-source on-state resistance <sup>a</sup>	В	V <sub>GS</sub> = 10 V, I <sub>D</sub> = 10 A	$\begin{array}{c ccccccccccccccccccccccccccccccccccc$			
Drain-source on-state resistance 4	R <sub>DS(on)</sub>	V <sub>GS</sub> = 4.5 V, I <sub>D</sub> = 10 A	-	0.0048	0.006	1 12
Forward transconductance <sup>a</sup>	9 <sub>fs</sub>	V <sub>DS</sub> = 15 V, I <sub>D</sub> = 10 A	-	50	-	S
Dynamic <sup>b</sup>						
Input capacitance	C <sub>iss</sub>		-	2000	-	
Output capacitance	C <sub>oss</sub>	$V_{DS} = 20 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ MHz}$	-	390	-	pF
Reverse transfer capacitance	C <sub>rss</sub>		-	18	-	
Total gate charge	0	$V_{DS} = 20 \text{ V}, V_{GS} = 10 \text{ V}, I_D = 10 \text{ A}$	-	27	41	
Total gate charge	$Q_g$		-	12.4	19	
Gate-source charge	Q <sub>gs</sub>	$V_{DS} = 20 \text{ V}, V_{GS} = 4.5 \text{ V}, I_{D} = 10 \text{ A}$	-	6.3	-	nC
Gate-drain charge	$Q_{gd}$ $Q_{oss}$ $V_{DS} = 20 \text{ V}, V_{GS} = 0 \text{ V}$		-	2.1	-	
Output charge	Q <sub>oss</sub>	V <sub>DS</sub> = 20 V, V <sub>GS</sub> = 0 V	-	16	-	
Gate resistance	Rg	f = 1 MHz	0.8	1.45	2.5	Ω
Turn-on delay time	t <sub>d(on)</sub>		-	12	24	
Rise time	t <sub>r</sub>	$V_{DD}$ = 20 V, $R_L$ = 2 $\Omega$ , $I_D \cong 10$ A,	-	5	10	
Turn-off delay time	t <sub>d(off)</sub>	$V_{GEN} = 10 \text{ V}, R_g = 1 \Omega$	-	25	50	
Fall time	t <sub>f</sub>		-	5	10	
Turn-on delay time	t <sub>d(on)</sub>		-	25	50	ris
Rise time	t <sub>r</sub>	$V_{DD}$ = 20 V, $R_L$ = 2 $\Omega$ , $I_D$ $\cong$ 10 A,	-	55	110	
Turn-off delay time	t <sub>d(off)</sub>	$V_{GEN}$ = 4.5 V, $R_g$ = 1 $\Omega$	-	22	44	
Fall time	t <sub>f</sub>		-	8	16	
<b>Drain-Source Body Diode Characteristi</b>	cs					
Continuous source-drain diode current	I <sub>S</sub>	T <sub>C</sub> = 25 °C	-	-	46.2	۸
Pulse diode forward current	I <sub>SM</sub>		-	-	150	Α
Body diode voltage	V <sub>SD</sub>	I <sub>S</sub> = 5 A, V <sub>GS</sub> = 0 V	-	0.74	1.1	V
Body diode reverse recovery time	t <sub>rr</sub>		-	24	48	ns
Body diode reverse recovery charge	Q <sub>rr</sub>	$I_F = 10 \text{ A}, \text{ di/dt} = 100 \text{ A/}\mu\text{s},$	-	13	26	nC
Reverse recovery fall time	ta	$T_J = 25  ^{\circ}C$	-	12	-	
Reverse recovery rise time	t <sub>b</sub>		-	12	-	ns

### Notes

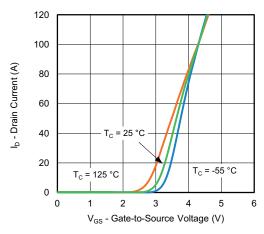
- a. Pulse test; pulse width  $\leq$  300  $\mu$ s, duty cycle  $\leq$  2 %
- b. Guaranteed by design, not subject to production testing

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

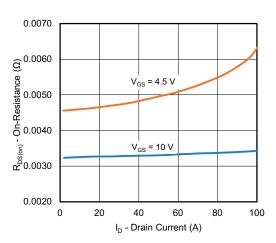




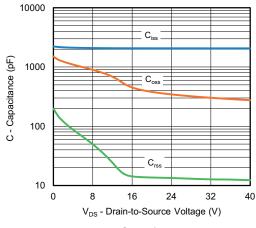
**Output Characteristics** 



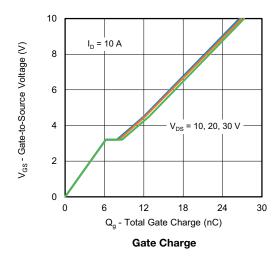
**Transfer Characteristics** 

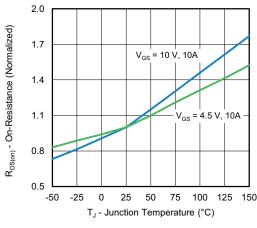


On-Resistance vs. Drain Current and Gate Voltage



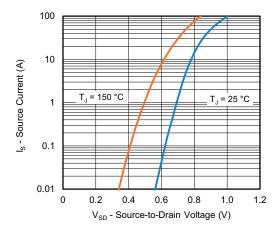
Capacitance



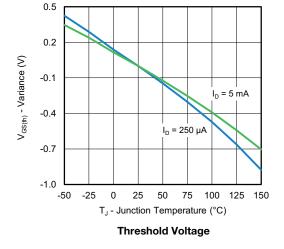


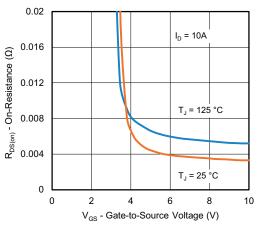
On-Resistance vs. Junction Temperature



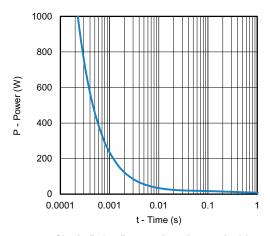


Source-Drain Diode Forward Voltage

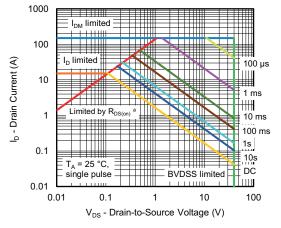




On-Resistance vs. Gate-to-Source Voltage

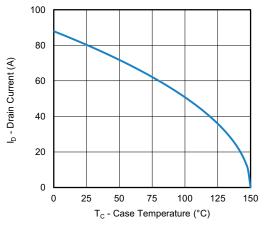


Single Pulse Power, Junction-to-Ambient

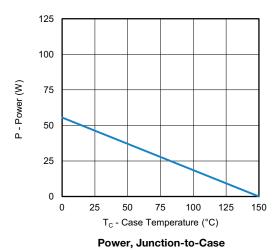


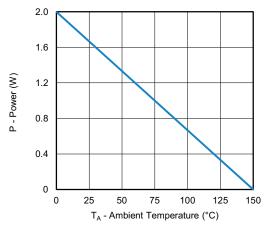
Safe Operating Area, Junction-to-Ambient





Current Derating a



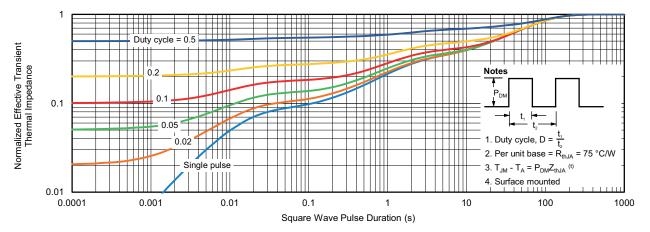


Power, Junction-to-Ambient

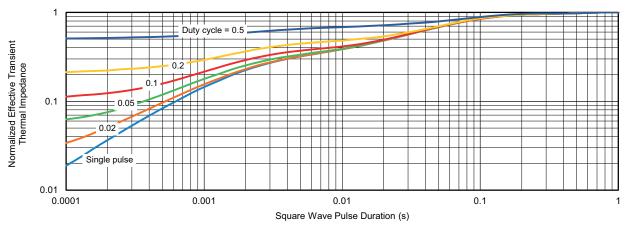
#### Note

a. The power dissipation P<sub>D</sub> is based on T<sub>J</sub> max. = 150 °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit





Normalized Thermal Transient Impedance, Junction-to-Ambient

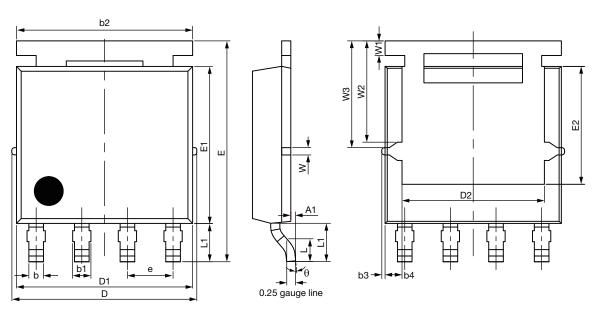


Normalized Thermal Transient Impedance, Junction-to-Case

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package / tape drawings, part marking, and reliability data, see <a href="https://www.vishay.com/ppg277516">www.vishay.com/ppg277516</a>.

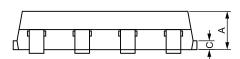


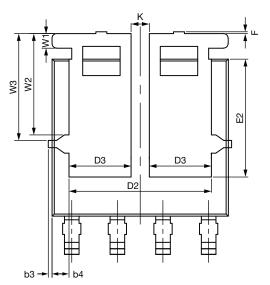
# PowerPAK® SO-8L Case Outline 1



Topside view

Backside view (single)





Backside view (dual)



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DIM	MILLIMETERS			INCHES			
DIM.	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.	
Α	1.00	1.07	1.14	0.039	0.042	0.045	
A1	0.00	-	0.127	0.00	-	0.005	
b	0.33	0.41	0.48	0.013	0.016	0.019	
b1	0.44	0.51	0.58	0.017	0.020	0.023	
b2	4.80	4.90	5.00	0.189	0.193	0.197	
b3		0.094	•		0.004		
b4		0.47			0.019		
С	0.20	0.25	0.30	0.008	0.010	0.012	
D	5.00	5.13	5.25	0.197	0.202	0.207	
D1	4.80	4.90	5.00	0.189	0.193	0.197	
D2	3.86	3.96	4.06	0.152	0.156	0.160	
D3	1.63	1.73	1.83	0.064	0.068	0.072	
е		1.27 BSC	•	0.050 BSC			
E	6.05	6.15	6.25	0.238	0.242	0.246	
E1	4.27	4.37	4.47	0.168	0.172	0.176	
E2	3.18	3.28	3.38	0.125	0.129	0.133	
F	-	-	0.15	-	-	0.006	
L	0.62	0.72	0.82	0.024	0.028	0.032	
L1	0.92	1.07	1.22	0.036	0.042	0.048	
K		0.51		0.020			
W	0.23		0.009				
W1	0.41			0.016			
W2	2.82			0.111			
W3		2.96			0.117		
θ	0°	-	10°	0°	-	10°	

ECN: S19-0643-Rev. E, 05-Aug-2019

DWG: 5976

#### Note

• Millimeters will gover



### RECOMMENDED MINIMUM PAD FOR PowerPAK® SO-8L SINGLE



Recommended Minimum Pads Dimensions in mm (inches)



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Vishay

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